NSN 5961-00-554-0267

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-554-0267 **Inclosure Material:** Ceramic and metal **Overall Length:** Between 0.340 inches and 0.376 inches Overall Diameter: Between 0.501 inches and 0.505 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 500.0 forward voltage, peak and 100.0 repetitive peak reverse voltage and 150.0 nonrepetitive peak reverse voltage and 2.0 gate trigger voltage, dc **Current Rating Per Characteristic:** 250.00 amperes forward current, average preset and 13.00 amperes forward current, total rms universal and 25.00 amperes forward current, total rms horsepower metric and 40.00 milliamperes forward current, total rms preset **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 tab, solder lug and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:** No